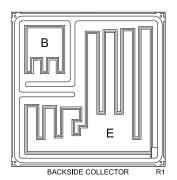


CP647-2N6287

PNP - Darlington Transistor Die 20 Amp, 100 Volt

The CP647-2N6287 die is a silicon PNP Darlington power transistor designed for high current applications.



MECHANICAL SPECIFICATIONS:

Die Size	211 x 211 MILS
Die Thickness	12.5 MILS
Base Bonding Pad Size	49 x 41 MILS
Emitter Bonding Pad Size	60 x 50 MILS
Top Side Metalization	AI – 50,000Å
Back Side Metalization	Ti/Ni/Ag - 1,000Å/6,000Å/10,000Å
Scribe Alley Width	4 MILS
Wafer Diameter	4 INCHES
Gross Die Per Wafer	246

MAXIMUM RATINGS: (T _A =25°C)	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	IC	20	Α
Peak Collector Current	I _{CM}	40	Α
Continuous Base Current	I _B	0.5	Α
Operating and Storage Junction Temperature	Tu. Tota	-65 to +150	°C

	ELECTRICAL	CHARACTERISTICS:	(T_{ℓ})	~=25°C unless	otherwise noted)
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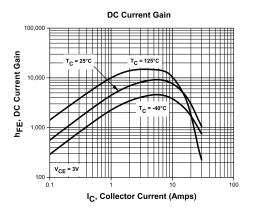
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
ICEX	V _{CE} =100V, V _{EB} =1.5V		0.5	mA
I _{CEO}	V _{CE} =50V		1.0	mA
I _{EBO}	V _{EB} =5.0V		2.0	mA
BV CEO	I _C =100mA	100		V
V _{CE(SAT)}	I _C =10A, I _B =40mA		2.0	V
V _{CE} (SAT)	I _C =20A, I _B =200mA		3.0	V
V _{BE(SAT)}	I _C =20A, I _B =200mA		4.0	V
V _{BE(ON)}	V_{CE} =3.0V, I_{C} =10A		2.8	V
hFE	V_{CE} =3.0V, I_{C} =10A	750	18K	
h _{FE}	V_{CE} =3.0V, I_{C} =20A	100		
h _{fe}	V_{CE} =3.0V, I_{C} =10A, f=1.0kHz	300		
f_{T}	V_{CE} =3.0V, I_{C} =10A, f=1.0MHz	4.0		MHz
C _{ob}	V _{CB} =10V, I _E =0, f=100kHz		600	pF

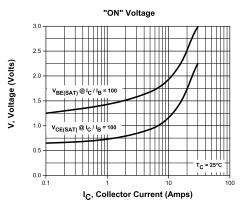
CP647-2N6287

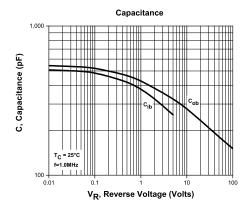
Typical Electrical Characteristics

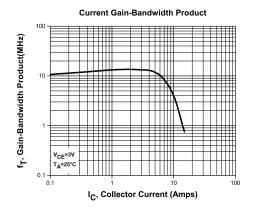


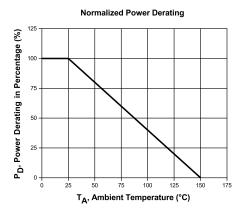
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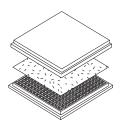






BARE DIE PACKING OPTIONS

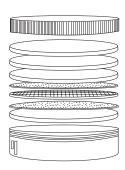




BARE DIE IN TRAY (WAFFLE) PACK

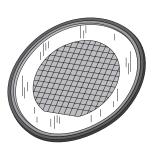
CT: Singulated die in tray (waffle) pack. (example: CP211-PART NUMBER-CT)

CM: Singulated die in tray (waffle) pack 100% visually inspected as per MIL-STD-750, (method 2072 transistors, method 2073 diodes). (example: CP211-PART NUMBER-CM)



UNSAWN WAFER

WN: Full wafer, unsawn, 100% tested with reject die inked. (example: CP211-PART NUMBER-WN)



SAWN WAFER ON PLASTIC RING

WR: Full wafer, sawn and mounted on plastic ring, 100% tested with reject die inked. (example: CP211-PART NUMBER-WR)

Please note: Sawn Wafer on Metal Frame (WS) is possible as a special order. Please contact your Central Sales Representative at 631-435-1110.



Visit the Central website for a complete listing of specifications: www.centralsemi.com/bdspecs

R2 (3-April 2017)

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- · Inventory bonding
- · Consolidated shipping options

- · Custom bar coding for shipments
- · Custom product packing

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Central's applications engineering team is ready to discuss your design challenges. Just ask.

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- SPICE models
- · Custom electrical curves
- Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- · Special wafer diffusions
- · PbSn plating options
- Package details
- · Application notes
- · Application and design sample kits
- · Custom product and package development

CONTACT US

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